## 1. General description

PNP high-voltage low  $V_{CEsat}$  transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8540Z-Q

### 2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- · Electronic ballast for fluorescent lighting
- · LED driver for LED chain module
- LCD backlighting
- · High Intensity Discharge (HID) front lighting
- Automotive motor management
- Hook switch for wired telecom
- Switch mode power supply

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	-	-500	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-400	V
I <sub>C</sub>	collector current		-	-	-0.25	Α
h <sub>FE</sub>	DC current gain	$V_{CE} = -10 \text{ V}; I_{C} = -50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	100	200	-	



500 V, 0.25 A PNP high-voltage low VCEsat transistor

## 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		в
3	Е	emitter		- Tw
4	С	collector	<b>□</b> 1 <b>□</b> 2 <b>□</b> 3	Ė
			SC-73 (SOT223)	sym028

## 6. Ordering information

#### Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBHV9040Z-Q		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223			

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBHV9040Z-Q	V9040Z

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-500	V
$V_{CEO}$	collector-emitter voltage	open base		-	-400	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-500	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-0.25	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-0.5	А
I <sub>BM</sub>	peak base current			-	-200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.7	W
			[2]	-	1.4	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

## 500 V, 0.25 A PNP high-voltage low VCEsat transistor

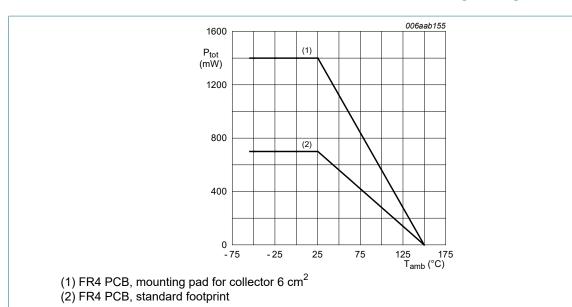


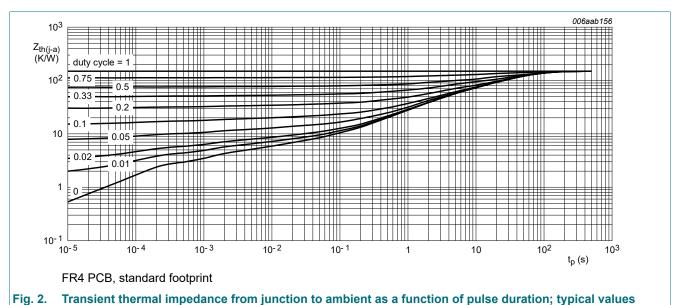
Fig. 1. Power derating curves

## 9. Thermal characteristics

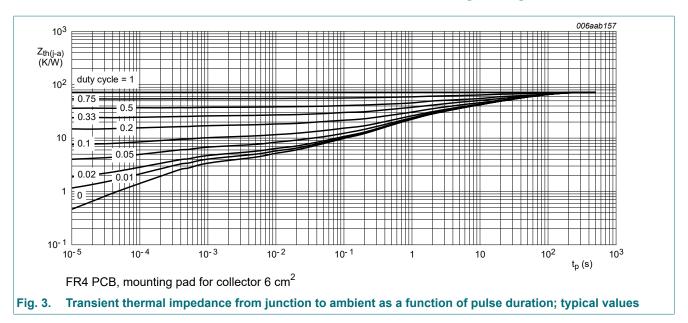
**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	175	K/W
	junction to ambient		[2]	-	-	89	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



### 500 V, 0.25 A PNP high-voltage low VCEsat transistor

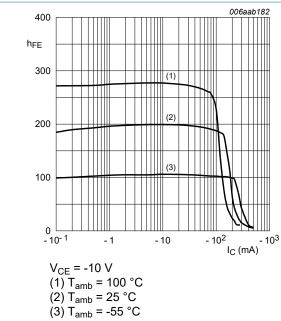


## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -320 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -320 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-10	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -4 \text{ V; } I_{C} = 0 \text{ A; } T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -320 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; $T_{amb}$ = 25 °C	100	200	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -100 mA; $T_{amb}$ = 25 °C	80	200	-	
		$V_{CE}$ = -10 V; $I_{C}$ = -250 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	10	25	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -100 mA; $I_B$ = -20 mA; $T_{amb}$ = 25 °C	-	-110	-200	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -100 mA; $I_B$ = -20 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-1	-1.1	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -2 V; I <sub>C</sub> = -0.15 A; I <sub>Bon</sub> = -0.03 A;	-	9	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 0.03 A; T <sub>amb</sub> = 25 °C	-	1810	-	ns
t <sub>on</sub>	turn-on time		-	1819	-	ns
ts	storage time		-	715	-	ns
t <sub>f</sub>	fall time		-	1085	-	ns
t <sub>off</sub>	turn-off time		-	1800	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	55	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -20 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C	-	7	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB}$ = -0.5 V; $I_{C}$ = 0 A; $i_{c}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C	-	150	-	pF

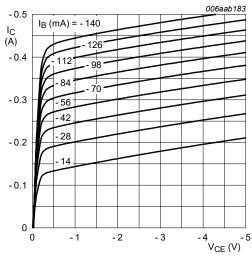
### 500 V, 0.25 A PNP high-voltage low VCEsat transistor



(2) 
$$T_{amb} = 25 \,^{\circ}C$$

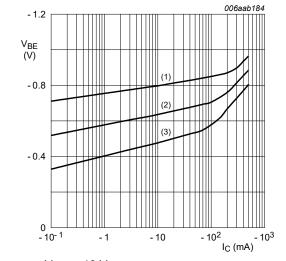
$$(3) T_{amb} = -55 °C$$

Fig. 4. DC current gain as a function of collector current; typical values



 $T_{amb}$  = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



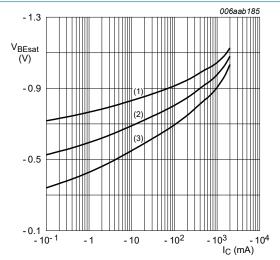
 $V_{CE}$  = -10 V

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

$$(1) T_{amb} = -55 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

### 500 V, 0.25 A PNP high-voltage low VCEsat transistor

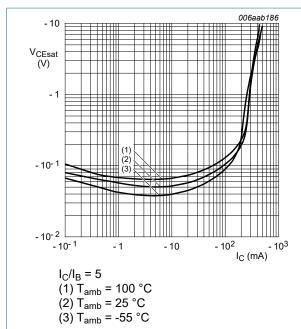


Fig. 8. Collector-emitter saturation voltage as a

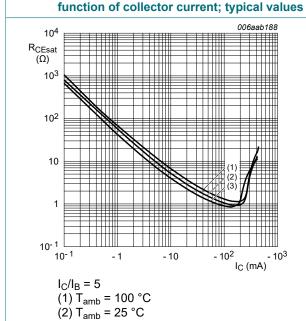


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

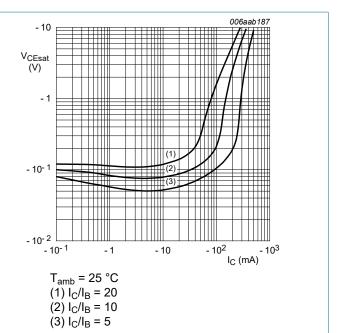


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

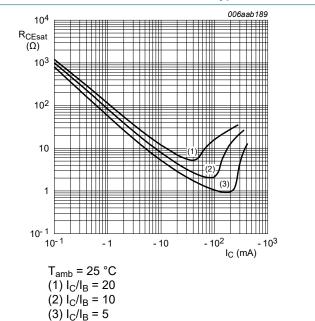
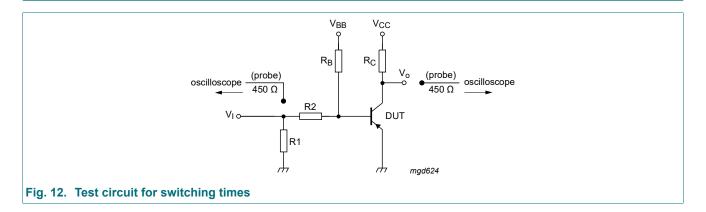


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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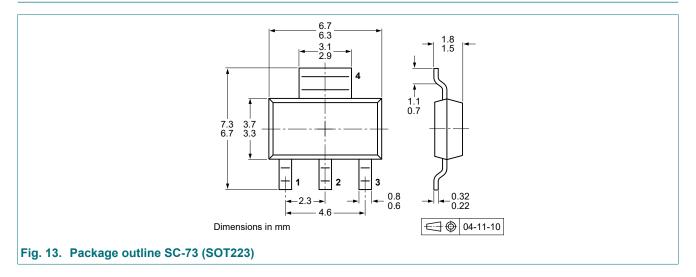
## 11. Test information



## **Quality information**

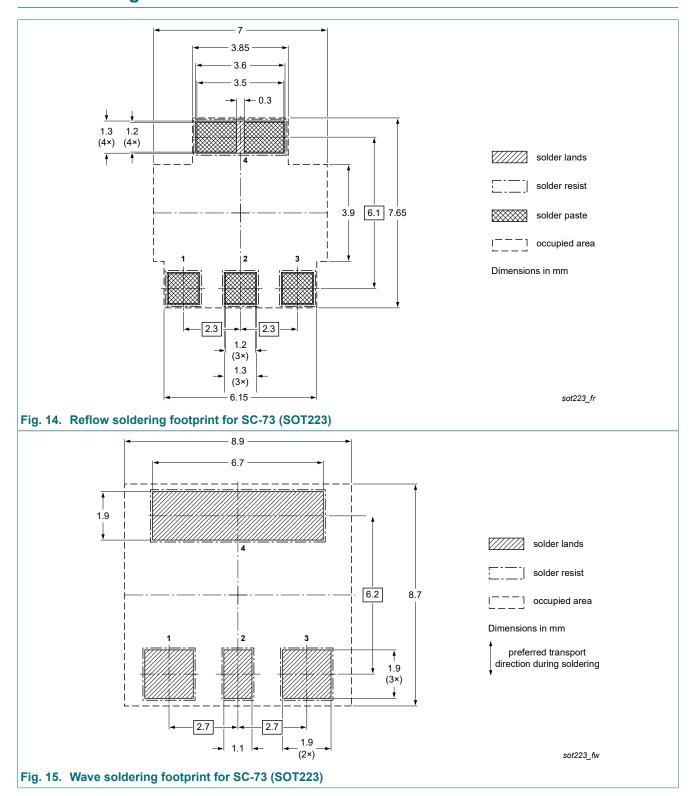
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 12. Package outline



## 500 V, 0.25 A PNP high-voltage low VCEsat transistor

# 13. Soldering



## 500 V, 0.25 A PNP high-voltage low VCEsat transistor

# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV9040Z-Q v.1	20230717	Product data sheet	-	-

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PBHV9040Z-Q

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 17 July 2023

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